

# 2SC5788

## Silicon NPN epitaxial planar type

Power supply for Audio & Visual equipments

such as TVs and VCRs

Industrial equipments such as DC-DC converters

### ■ Features

- High-speed switching ( $t_{stg}$ : storage time/ $t_f$ : fall time is short)
- Low collector to emitter saturation voltage  $V_{CE(sat)}$
- Superior forward current transfer ratio  $h_{FE}$  linearity
- Allowing automatic insertion with radial tapering

### ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	60	V
Collector-emitter voltage (Base open)	$V_{CEO}$	60	V
Emitter-base voltage (Collector open)	$V_{EBO}$	6	V
Collector current	$I_C$	3	A
Peak collector current	$I_{CP}$	6	A
Collector power dissipation	$P_C$	$T_C = 25^\circ\text{C}$	15
		$T_a = 25^\circ\text{C}$	2
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 ~ +150	$^\circ\text{C}$

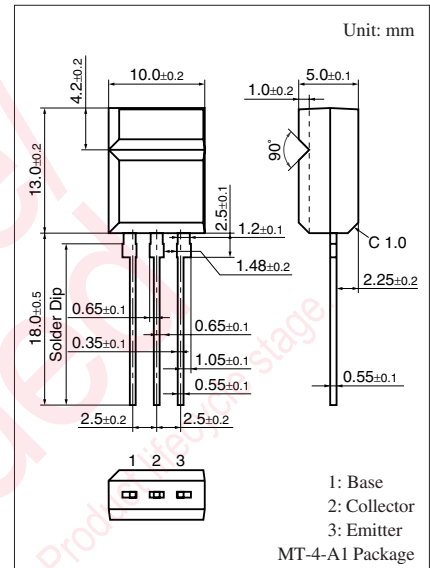
### ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 60 \text{ V}, I_E = 0$			100	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 60 \text{ V}, I_B = 0$			100	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_C = 0$			1	mA
Forward current transfer ratio	$h_{FE1}^*$	$V_{CE} = 4 \text{ V}, I_C = 1 \text{ A}$	120		320	—
	$h_{FE2}$	$V_{CE} = 4 \text{ V}, I_C = 3 \text{ A}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 3 \text{ A}, I_B = 375 \text{ mA}$			0.8	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_C = 0.1 \text{ A}, f = 10 \text{ MHz}$		180		MHz
Turn-on time	$t_{on}$	$I_C = 1 \text{ A}, \text{Resistance loaded}$		0.2	0.3	$\mu\text{s}$
Storage time	$t_{stg}$	$I_{B1} = 0.1 \text{ A}, I_{B2} = -0.1 \text{ A}$		0.55	0.7	$\mu\text{s}$
Fall time	$t_f$	$V_{CC} = 50 \text{ V}$		0.1	0.15	$\mu\text{s}$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

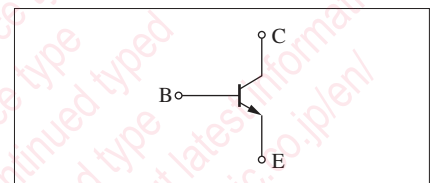
2. \*: Rank classification

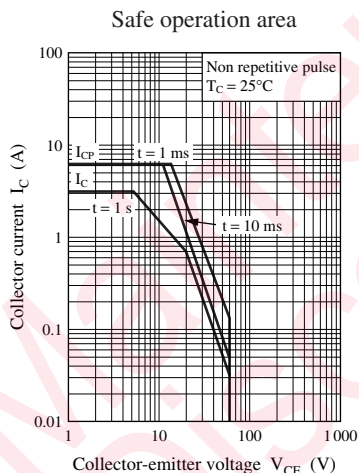
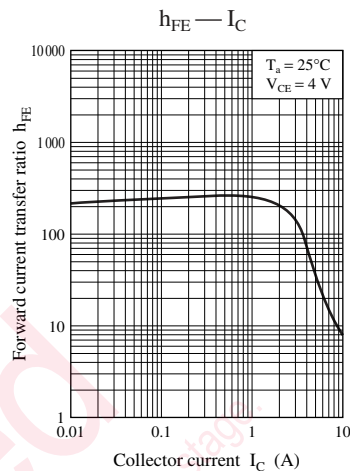
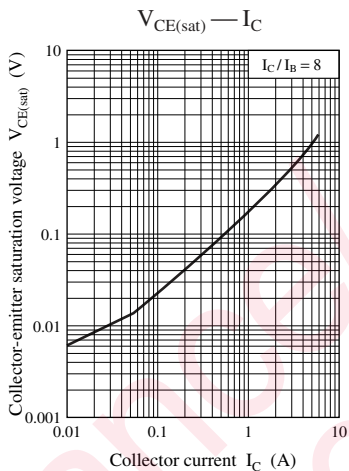
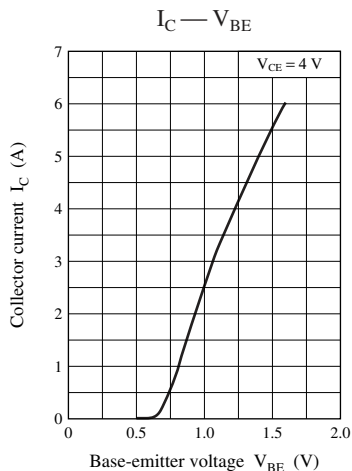
Rank	P	Q
$h_{FE1}$	160 to 320	120 to 250



Marking Symbol: C5788

Internal Connection





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